

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|---|------|-----|------|--|---|---------------------|----------|------------------|--------|
| 1 | BRS | L1 | 696 | (vary or variation or change\$3 or alter\$3) with ("wt %" or "%" or percent\$3 or concentration) with (((peroxide or H2O2 or "H.sub.2O.sub.2") same (NH4OH or ammonia or "ammonium hydroxide" or "NH.sub.4OH") same (HF of hydrofluoric or "hydrogen fluoride") same (phosphoric or H3PO4 or "H.sub.3PO.sub.4")) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 11:18 | | | |
| 2 | BRS | L2 | 0 | (vary or variation or change\$3 or alter\$3) with ("wt %" or "%" or percent\$3 or concentration) with (((peroxide or H2O2 or "H.sub.2O.sub.2") same (NH4OH or ammonia or "ammonium hydroxide" or "NH.sub.4OH") same (HF of hydrofluoric or "hydrogen fluoride") same (phosphoric or H3PO4 or "H.sub.3PO.sub.4")) same etch\$3) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 11:19 | | | |
| 3 | BRS | L3 | 5 | ("wt %" or "%" or percent\$3 or concentration) with (((peroxide or H2O2 or "H.sub.2O.sub.2") same (NH4OH or ammonia or "ammonium hydroxide" or "NH.sub.4OH") same (HF of hydrofluoric or "hydrogen fluoride") same (phosphoric or H3PO4 or "H.sub.3PO.sub.4")) same etch\$3) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 11:55 | | | |
| 4 | BRS | L4 | 0 | ("wt %" or "%" or percent\$3 or concentration) with (((peroxide or H2O2 or "H.sub.2O.sub.2") same (NH4OH or ammonia or "ammonium hydroxide" or "NH.sub.4OH") same (HF of hydrofluoric or "hydrogen fluoride") same (phosphoric or H3PO4 or "H.sub.3PO.sub.4")) same etch\$3 same temperature) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 11:55 | | | |
| 5 | BRS | L5 | 427 | etch\$3 same (("wt %" or "%") with (phosphoric or H3PO4 or "H.sub.3PO.sub.4")) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 11:56 | | | |
| 6 | BRS | L6 | 16 | etch\$3 same (("wt %" or "%") with (phosphoric or H3PO4 or "H.sub.3PO.sub.4")) with (nitride or SiN or Si3N4 or "Si.sub.3N.sub.4") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 12:16 | | | |

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|----|------|-----|------|--|--|------------------|----------|------------------|--------|
| 7 | BRS | L7 | 4 | etch\$3 same (("wt %" or "%") with ((phosphoric or H3PO4 or "H.sub.3PO.sub.4") and (HF or hydrofluoric or "hydrogen fluoride"))) with (nitride or SiN or Si3N4 or "Si.sub.3N.sub.4")) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 12:53 | | | |
| 8 | BRS | L8 | 3875 | ((fill\$3 or deposit\$3) with polysilicon) same (cmp or polish\$3 or planariz\$5) same (SAC or (self adj align\$4) or "contact hole" or hole or open\$3 or node or nodal) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 12:57 | | | |
| 9 | BRS | L9 | 2489 | ((fill\$3 or deposit\$3) with polysilicon) with (SAC or (self adj align\$4) or "contact hole" or hole or open\$3 or node or nodal)) same (cmp or polish\$3 or planariz\$5) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 12:58 | | | |
| 10 | BRS | L10 | 1771 | ((fill\$3 or deposit\$3) with polysilicon) with (SAC or (self adj align\$4) or "contact hole" or hole or open\$3 or node or nodal)) same (cmp or polish\$3 or planariz\$5) same etch\$3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 13:00 | | | |
| 11 | BRS | L11 | 1088 | 10 and @pd<="20031114" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 13:02 | | | |
| 12 | BRS | L12 | 455 | ((fill\$3 or deposit\$3) with polysilicon) with (SAC or (self adj align\$4) or "contact hole" or hole or open\$3 or node or nodal)) same (cmp or polish\$3 or planariz\$5) same etch\$3 same (source and drain) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 13:48 | | | |
| 13 | BRS | L13 | 291 | 12 and @pd<="20031114" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 13:51 | | | |
| 14 | BRS | L14 | 1598 | ((fill\$3 or deposit\$3) with polysilicon) with (SAC or (self adj align\$4) or "contact hole" or hole or open\$3 or node or nodal)) same (cmp or ((chemical\$2 adj mechanical\$2) adj (planariz\$5 or polish\$3))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 13:48 | | | |

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|----|------|-----|------|---|---|---------------------|----------|------------------|--------|
| 15 | BRS | L15 | 284 | ((fill\$3 or deposit\$3) with polysilicon) with (SAC or (self adj align\$4) or "contact hole" or hole or open\$3 or node or nodal)) same (cmp or ((chemical\$2 adj mechanical\$2) adj (planariz\$5 or polish\$3))) same etch\$3 same (source and drain) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 13:48 | | | |
| 16 | BRS | L16 | 167 | 15 and @pd<="20031114" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2007/03/12 13:51 | | | |